Since 🛨 1968

SEMICOR

Trusted Everywhere for Mission Success

Semicoa Product Overview

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TRANSISTOR HIGHLIGHTS



- Rad Hard Products
 - Broadest QPL offering (41 transistor part numbers)
 - JANTXV and JANS levels
 - Our RHA is designed around space program requirements which greatly exceeds
 MIL-PRF-19500 limits
 - Rad Hard By Design (RHBD)
 - All products are classified as EAR99 for export!
- Fab Assembly Test US based for JANS
- Overall production capacity has more than doubled
- Over 1,100 part numbers on the QPL
 - 928 packaged parts
 - 191 die part numbers (HC & KC)



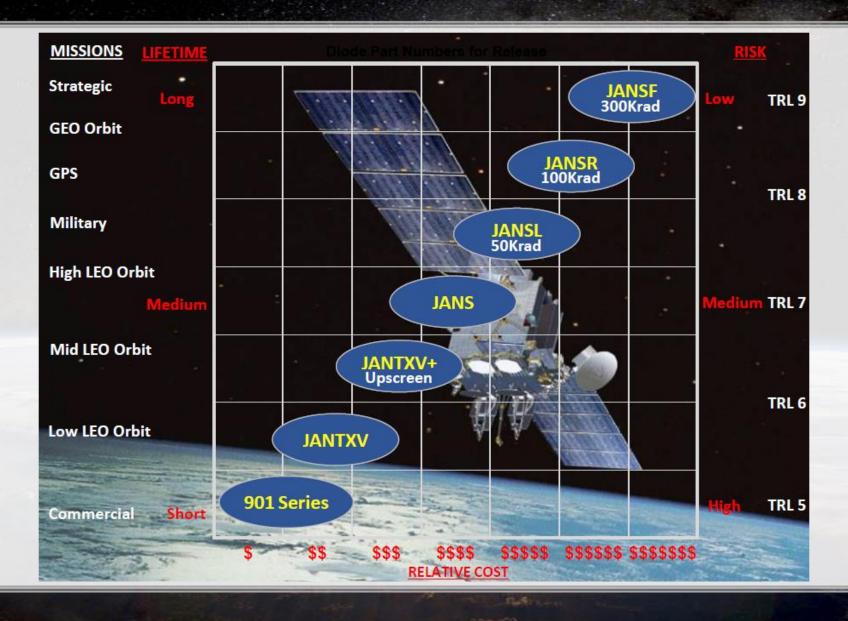
Semicoa's Rad Hard Bipolar Transistor Product Offering

JANS Part Number & Packages	Polarity	Rad Level	JANS Part Number & Packages	Polarity	Rad Level
2N2218, A, AL	NPN	100 Krad(Si)	2N3737, UB	NPN	300 Krad(Si)
2N2219, A, AL	NPN	100 Krad(Si)	2N3810, L, U	PNP	100 Krad(Si)
2N2221A, AL, AUA, AUB, AUBC	NPN	300 Krad(Si)	2N3811, L, U	PNP	100 Krad(Si)
2N2222A, AL, AUA, AUB, AUBC	NPN	300 Krad(Si)	2N3866, A, UB, AUB	NPN	300 Krad(Si)
2N2369A, AUB, AUBC	NPN	300 Krad(Si)	2N4029	PNP	300 Krad(Si)
2N2484, UB, UBC	NPN	300 Krad(Si)	2N4033, UB	PNP	300 Krad(Si)
2N2857, UB	NPN	300 Krad(Si)	2N4261, UB, UBC	PNP	300 Krad(Si)
2N2904A, AL	PNP	300 Krad(Si)	2N4449	NPN	300 Krad(Si)
2N2905A, AL	PNP	300 Krad(Si)	2N4957, UB	PNP	300 Krad(Si)
2N2906A, AL, AUA, AUB, AUBC	PNP	300 Krad(Si)	2N5151, L	PNP	300 Krad(Si)
2N2907A, AL, AUA, AUB, AUBC	PNP	300 Krad(Si)	2N5152, L	NPN	300 Krad(Si)
2N2919, L, U	NPN	100 Krad(Si)	2N5153, L	PNP	300 Krad(Si)
2N2920, L, U	NPN	100 Krad(Si)	2N5154, L	NPN	300 Krad(Si)
2N2946A	PNP	100 Krad(Si)	2N5794UC, AUC	NPN	300 Krad(Si)
2N3019, S	NPN	300 Krad(Si)	2N6193	PNP	300 Krad(Si)
2N3057A	NPN	300 Krad(Si)	2N6987	PNP	300 Krad(Si)
2N3501, L, UB	NPN	300 Krad(Si)	2N6988	PNP	300 Krad(Si)
2N3635, L, UB	PNP	300 Krad(Si)	2N6989	NPN	100 Krad(Si)
2N3637, L, UB	PNP	300 Krad(Si)	2N6990	NPN	100 Krad(Si)
2N3700, UB	NPN	300 Krad(Si)	2N918, UB	NPN	300 Krad(Si)
2N3735, L	NPN	300 Krad(Si)			

All devices available in JANTXV and JANS plus Radiation Hardness Semicoa has the Broadest Rad Hard Product Offering on MIL-PRF-19500!

MISSION-RISK-COST TRADESPACE



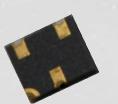


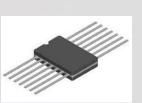
TRANSISTOR HIGHLIGHTS

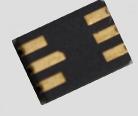


- Through Hole, Surface Mount, and **Bare Die Options**
- Solutions for Legacy components
- Custom Design Products
- Radiation Qualification
- **Industry Benchmark Radiation** Hardness Assured (RHA) Program











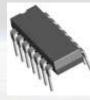
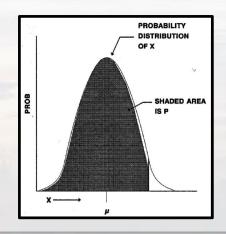


	TABLE E-VIII. Group D inspection (RHA inspections)					
l r		MIL-STD-750	JANS	JANTXV		
	Test			Quantity	Quantity	
	lest	Method	Condition	(Accept	(Accept	
				Number)	Number)	
	Subgroup 2 Steady-state total dose irradiation Conformance	1019	+25°C	4(0)	11(0)	
	inspection			2(0)	(e)	
	End-point electrical parameters		As specified in accordance with specification sheet			

Test 11 samples per wafer for all RHA Product!

Acceptance based on 0.99/90% statistics for endpoints and deltas

Group D endpoints plus $\Delta P = P_{PostRad} - P_{PreRad}$



RHBD TRANSISTORS



- Radiation Hardened By Design (RHBD)
 - Standard Technology modified to improve radiation performance
- Optimized for Total Dose Hardness including LDR
 - Minimize amount of trapped charge and reduce the impact of that charge on the junction performance
 - Radiation performance 10X better than standard technology
 - No impact on Displacement Damage performance
- RHBD Product Features
 - Common Die layout as Standard Technology
 - Qualified to the same slash sheet as Standard Technology
 - No enhancement for Low Dose Rate @10 mrad/s

Space qualified, Space heritage, Trusted Everywhere for Mission Success



LDR QUALIFIED TRANSISTORS

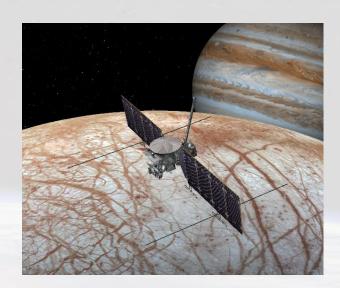


- JANTXV + RHA, JANS + RHA
- Tested to Low Dose Rate (LDR)
 - Every wafer/lot qualified
 - 10/30/50/100 Krad, higher if needed
 - 10 or 100 mrad(Si)
 - 11 biased & 11 unbiased
 - Room & High Temperature Anneal
 - Group D parameters and conditions
 - Customer options can be added
- Marked with MIL-PRF-19500 or SCD part number
- Available for the entire product line





- Nasa Mission to Europa a moon of Jupiter
- Significant radiation challenge
- Semicoa RHBD utilized for bipolar transistors based on radiation performance (HDR and LDR)
 - 2N2222AUB, 2N2369AUB, 2N2484AUB, 2N2907AUB, 2N3501UB, 2N3637UB, 2N4261UB
- Tested to the Mission Requirements
 - HDR tested to 300 Krad (JANSF)
 - LDR tested to 100 Krad at 10 mrad/s and then 45 mrad/s up to 300 Krad
 - Dose end points: 10, 30, 50, 100, 150, 200, 225, 250, 275, 300 Krad
 - Annealing after radiation for 168 hours at room temperature
 - 11 samples biased at 80% VCEO and 11 samples with no bias
 - Parameters and Conditions are MIL-PRF-19500 Slash Sheet and ESCC Detail
 Specifications (where application for Rad Hard parts)
- Parts marked as MIL-PRF-19500 JANSF with LDR C of C
- Semicoa holds qualified wafers for all program contractors



901 Series

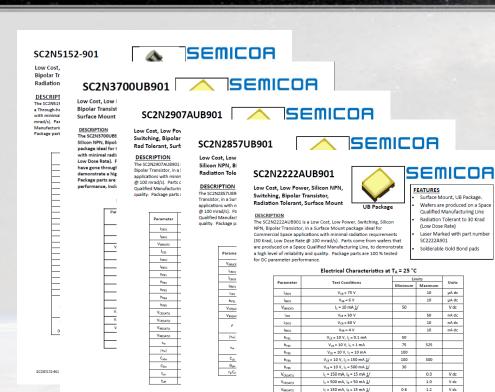
- Low Cost option targeted for High Volume Large Constellation/Commercial Space applications
- Surface mount package and through hole packages available
- Wafer fabrication flow identical to JANS wafers using same JANS wafer fab
- Wafers selected based on sample evaluation which includes DC, AC electrical characterization, HTRB, Burn-In, High Temperature Life, and Steady State Operational Life tests
- Assembled in QML Certified Production facility in Hermetic Packaging
- Packaged devices tested for DC parameters with high and low temperature screening
- Laser marked (no serialization)
- Product family certified as radiation tolerant to 30 krad low dose rate total dose based upon years of historical data





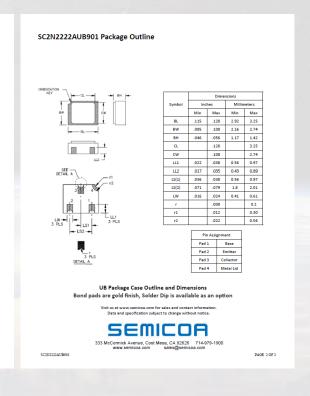
LARGE CONSTELLATION SPACE





SC2N3700UB901

Data Sheet Examples



PAGE 1 OF 2

FEATURES

SC2222A901

10 μA dc

300

1.0

Ic = 500 mA, Is = 50 mA 1/

Vcs = 10 V, Ic = 1 mA, f = 1 kHz Vcr = 20 V. Ic = 20 mA. f = 100 MHz $V_{CR} = 10 \text{ V}, I_g = 0, 100 \text{ kHz} \le f \le 1 \text{ MHz}$

 $V_{E8} = 0.5 \text{ V}, I_C = 0, 100 \text{ kHz} \le f \le 1 \text{ MHz}$

1/ Pulse condition: Pulse width < 300 μs, duty cycle < 2%

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t_{on} V_{CC} = 30 V, V_{BE} = 0.5 V, I_C = 150 mA, I_{B1} = 15 mA t_{off} V_{cc} = 30 V, I_c = 150 mA, I₈₁ = I₈₂ = 15 mA Surface Mount, UB Package.

Wafers are produced on a Space

Qualified Manufacturing Line

Radiation Tolerant to 30 Krad

Laser Marked with part numbe

Solderable Gold Bond pads

nA dc

LARGE CONSTELLATION SPACE



901 Series Space Product Flow

WAFER QUALIFICATION

00: 00::00 of			
WAFER QUALIFICATION PROCESS FLOW			
Wafer Production			
Class Probe			
Pull samples from each Wafer			
Die Visual Inspection			
Die Attach			
Wire Bond			
Internal Visual			
Capping			
Laser Mark			
DC Electrical Test			
AC Electrical Test			
High Temperature Reverse Bias			
DC Electrical Test			
Burn-In			
DC Electrical Test			
High Temperature Life			
DC Electrical Test			
Steady State Operation Life			
DC Electrical Test			
Engineering Review and Approval			

ASSEMBLY AND TEST FLOW			
Wafer Selection			
Wafer Saw			
Die Visual Inspection			
Die Attach			
Wire Bond			
Internal Visual Inspection			
Pre-Moisture Bake			
Thermal Vacuum Bake			
Lid Seal			
Visual Inspection			
Stabilization Bake			
Laser Mark			
DC Electrical Test (100%)			
Sample AC Electrical Test (45/0 or 90/1)			
Sample Burn In (45/0 or 90/1)			
Sample High & Low Temperature Test (45/0 or 90/1)			
Sample DC Electrical Test (45/0 or 90/1)			
Engineering Review			
Packing for Shipment			

DEVICE QUALIFICATION

SEMICOA INNOVATION - GLASSLESS DIODE PACKAGE SEMICOA

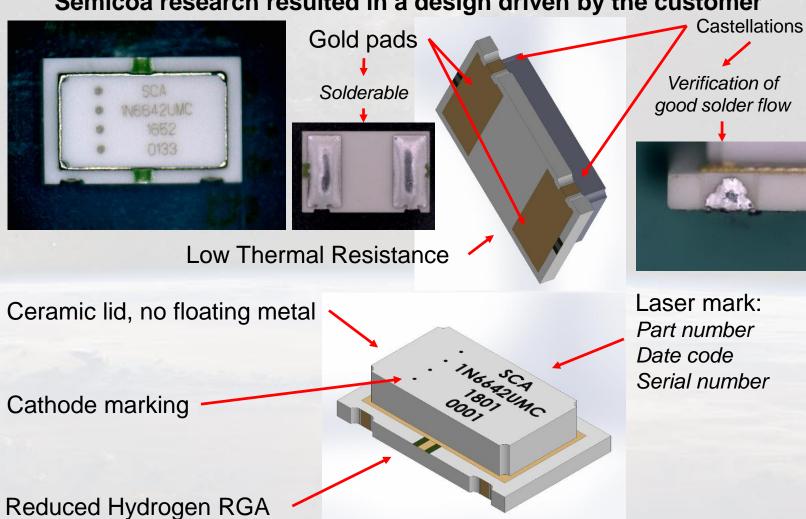
- Semicoa revolutionizes Diode packages for Space !!!
- Semicoa ceramic UMC package is now JANS QPL available for the /477 family of ultrafast rectifiers: 1N5802/1N5804/1N5806
- HC and KC die QPL available: 1N5614, 1N5615, 1N5802, 1N5804, 1N5806
- Product samples available for customer qualifications



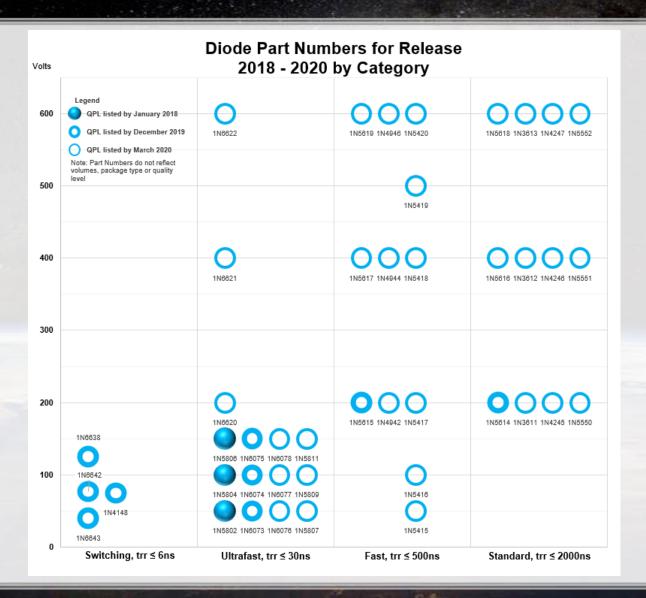


UMC PACKAGE KEY FEATURES

Semicoa research resulted in a design driven by the customer



ALL JANS QUALIFIED

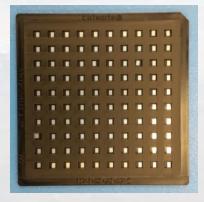


DRIVEN BY PROGRAM DEMAND

FAQ's & SHIPPING OPTIONS



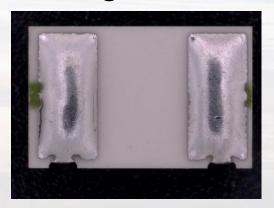
- Semicoa proven construction methods used to assemble these packages
- Laser marked with serial number- NO EXTRA CHARGE!
- Fine and Gross Leak, Red Dye, RGA NO PROBLEM!!!
- Semicoa is giving you more choices by adding the UMC package to existing DLA Slash Sheets
- HC & KC Die form available in waffle pack
- Tape and Reel option for packaged devices
- Solder Dip option complying to Semicoa most stringent standards



Die in waffle pack



Packages in waffle pack



Solder dipped option

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COMPARISON OF PRODUCT FLOWS

SEMICOA

SMALLSAT
"901" Series

LASER MARK NO SERIAL NUMBER (100%)

DC ELECTRICAL TEST OF LOT (100%)

AC TEST (N=45/0, 90/1)

BURN IN
(48 HRS, TJ=135°C)
(N=45/0, 90/1)
HI/LOW TEMPERATURE TEST
(N=45/0, 90/1)
DC ELECTRICAL
(N=45/0, 90/1)

ENGINEERING REVIEW

SHIP

901 Wafers are the same as JANS qualified products!

	MIL-PRF-19500 JANTXV		
-	LASER MARK NO SERIAL NUMBER (100%)	SNAP & BREAK	
	EXTERNAL V & M	GROSS LEAK	
	LASER DEFECTS ONLY	(100%)	
	(N=22, C=0)	FINE LEAK	
	X-RAY	(100%)	
	LASER DEFECTS ONLY	RED DYE	
	(N=22, C=0)	(100%)	
	CDOSC LEAK	FINAL ELECTRICAL	
	GROSS LEAK	(N=116, C=0, GO/NO GO)	
	(N=22, C=0)	(IF C>0, 100%)	
	FINE LEAK	GROUP A1	
	(N=22, C=0)	(N=116, C=0)	
	RED DYE	GROUP A2-DC	
	(N=22, C=0)	(N=116, C=0, READ & RECORD)	
	FIRST ELECTRICAL	GROUP A3-TEMP	
	(N=200, PDA<3%, READ &	(N=116, C=0, READ & RECORD)	
	RECORD)	DC ELECTRICAL, END POINTS	
	(100%, GO/NO GO, PDA>3%)	(N=116, C=0, GO/NO GO)	
	TEMPERATURE CYCLE	GROUP A4-AC	
	(100%, -55°C, +175°C, 20 CYCLES)	(N=116, C=0, READ & RECORD)	
	HTRB	(N-110, C-0, READ & RECORD)	
	(100%, 48 HRS, +150°C)	DC ELECTRICAL, END POINTS	
	PRE-BURN IN ELECTRICAL TEST	(N=116, C=0, GO/NO GO)	
	(100%, READ & RECORD)	RGA	
	PDA	NGA	
	(ACCPT<10%)	GROUP B	
	BURN-IN	GROOF B	
	(100%, 160 HRS, TJ=135°C)	GROUP C	
	POST-BURN-IN ELECTRICAL TEST		
	(100%, READ & RECORD)	GROUP D-RADIATION (A/R)	
	DELTA ANALYSIS	JANTXV ONLY	
	PDA	GROUP E (QUAL/REQUAL)	
	(ACCPT<10%)	FINAL INSPECTION	
	3-SIGMA ANALYSIS	SHIP	

MIL-PRF-19500 JANS	
FIRST ELECTRICAL	SOLDERABILITY TEST
(100%, GO/NO GO)	(N=15, C=0)
LACED AND REAL PROPERTY.	GROSS LEAK
LASER MARK W/SERIAL NUMBER	(100%)
(100%)	, ,
TEMPERATURE CYCLE	FINE LEAK
(100%, -55°C, +175°C, 20 CYCLES)	(100%)
	RED DYE
PRE-HTRB ELECTRICAL TEST	(100%)
(100%, READ & RECORD)	X-RAY
HTRB	(100%)
(100%, 48 HRS, +150°C)	ANNEAL
POST-HTRB ELECTRICAL TEST	24 HOURS, 200°C
(100%, READ & RECORD)	DC ELECTRICAL
	(100%, C=0, READ & RECORD)
DELTA ANALYSIS	EXTERNAL VISUAL & MECHANICAL (100%)
PDA	GROUP A1
(ACCPT<5%)	(N=15, C=0)
BURN-IN	GROUP A2-DC
(100%, 240 HRS, TJ=135°C)	(N=116, C=0, READ & RECORD)
POST-BURN-IN ELECTRICAL TEST	GROUP A3-TEMP
(100%, READ & RECORD)	(N=116, C=0, READ & RECORD)
DELTA ANALYSIS	DC ELECTRICAL, END POINTS
PDA	(N=116, C=0, READ & RECORD)
(ACCPT<5%)	GROUP A4-AC
	(N=116, C=0, READ & RECORD)
3-SIGMA ANALYSIS	END POINTS/DC ELECTRICAL
TEMPERATURE TEST	(N=116, C=0, READ & RECORD)
(100%, READ & RECORD)	RGA
END POINTS/DC ELECTRICAL	GROUP B
(100%, GO/NO GO)	GROUP C
SNAP & BREAK	GROUP D-RADIATION (A/R)
CONSTANT ACCELERATION	GROUP E (QUAL/REQUAL)
(100%, Y1, 20KG's)	FINAL INSPECTION
PIND	SHIP
(100%)	אוחכ